AON6280

80V N-Channel AlphaSGT™

General Description

The AON6280 uses trench MOSFET technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$, Ciss and Coss. This device is ideal for boost converters and synchronous rectifiers for consumer, telecom, industrial power supplies and LED backlighting.

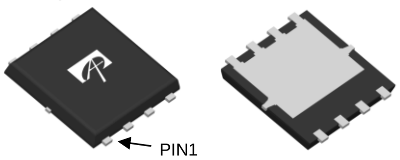
Product Summary

V_{DS}	80V
I_D (at V_{GS}=10V)	85A
$R_{DS(ON)}$ (at V_{GS}=10V)	< 4.1mΩ
$R_{DS(ON)}$ (at V_{GS}=6V)	< 5.0mΩ

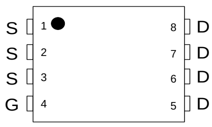
100% UIS Tested
100% R_g Tested

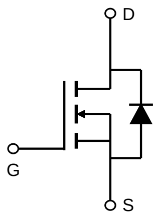
DFN5X6

Top View Bottom View



Top View





Absolute Maximum Ratings T_A=25°C unless otherwise noted				
Parameter		**Symbol**	**Maximum**	**Units**
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C=25°C	I_D	100	A
	T_C=100°C		65	
Pulsed Drain Current [C]		I_{DM}	230	
Continuous Drain Current	T_A=25°C	I_{DSM}	17	A
	T_A=70°C		13	
Avalanche Current [C]		I_{AS}	50	A
Avalanche energy L=0.1mH [C]		E_{AS}	125	mJ
Power Dissipation [B]	T_C=25°C	P_D	83	W
	T_C=100°C		33	
Power Dissipation [A]	T_A=25°C	P_{DSM}	7.3	W
	T_A=70°C		4.7	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics					
Parameter		**Symbol**	**Typ**	**Max**	**Units**
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	14	17	°C/W
Maximum Junction-to-Ambient [A D]	Steady-State		40	55	°C/W
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	1	1.5	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V		80			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=80V, V_{GS}=0V				1	µA
			T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±20V				±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250µA		2	2.6	3.2	V
$I_{D(ON)}$	On state drain current	V_{GS}=10V, V_{DS}=5V		230			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=20A			3.4	4.1	mΩ
			T_J=125°C		5.8	7	
		V_{GS}=6V, I_D=20A			4	5	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A			76		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V			0.7	1	V
I_S	Maximum Body-Diode Continuous Current					95	A
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=40V, f=1MHz			3930		pF
C_{oss}	Output Capacitance				592		pF
C_{rss}	Reverse Transfer Capacitance				66		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		0.3	0.7	1.1	Ω
SWITCHING PARAMETERS							
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=40V, I_D=20A			58	82	nC
Q_{gs}	Gate Source Charge				15		nC
Q_{gd}	Gate Drain Charge				14		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=40V, R_L=2Ω, R_{GEN}=3Ω			13		ns
t_r	Turn-On Rise Time				6		ns
$t_{D(off)}$	Turn-Off DelayTime				32		ns
t_f	Turn-Off Fall Time				9		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=20A, dI/dt=500A/µs			36		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=20A, dI/dt=500A/µs			153		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The Power dissipation P_{DSM} is based on R $_{\theta JA}$ and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J =25° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.
G. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

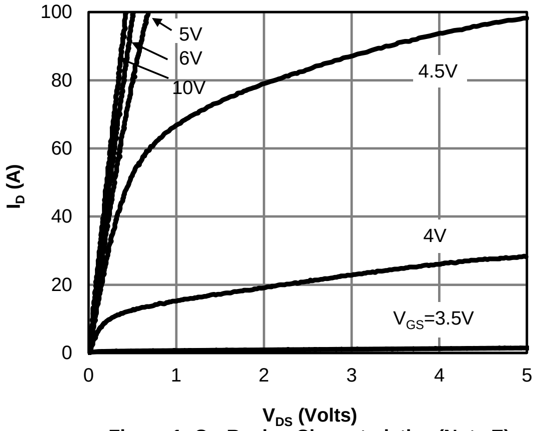


Figure 1: On-Region Characteristics (Note E)

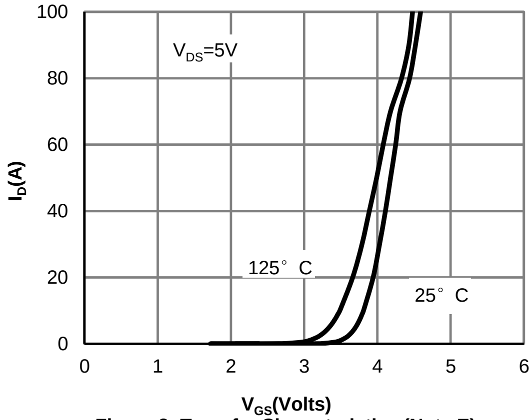


Figure 2: Transfer Characteristics (Note E)

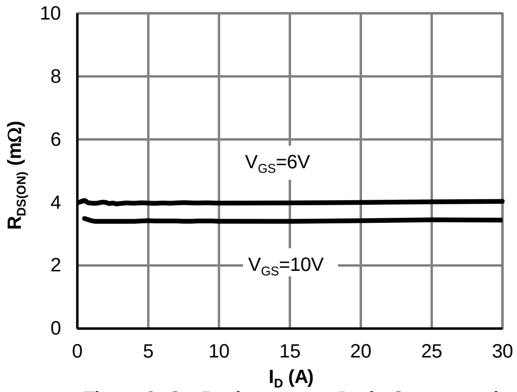


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

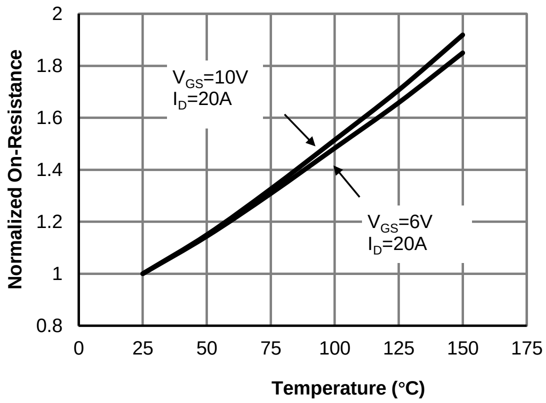


Figure 4: On-Resistance vs. Junction Temperature (Note E)

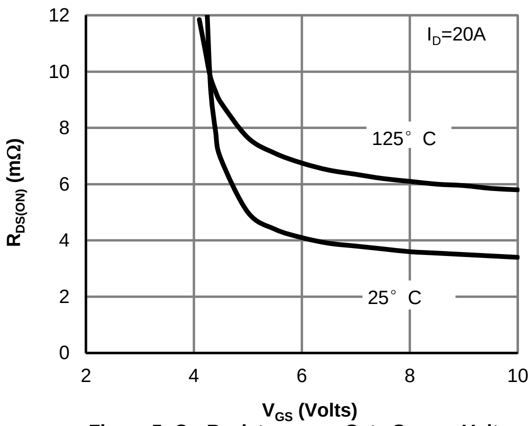


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

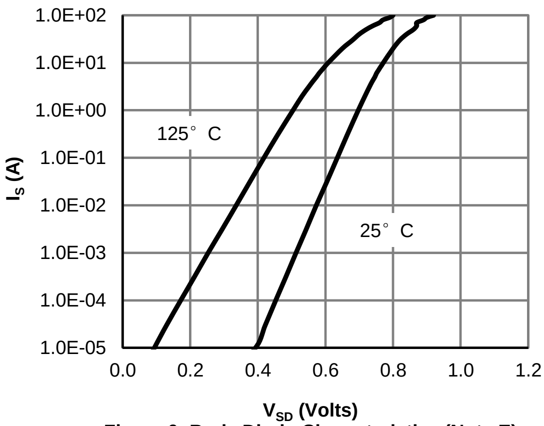


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

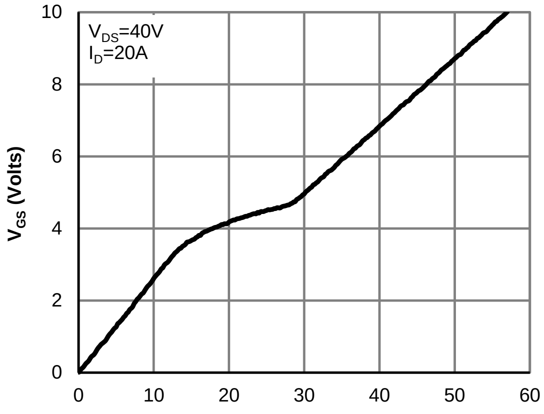


Figure 7: Gate-Charge Characteristics

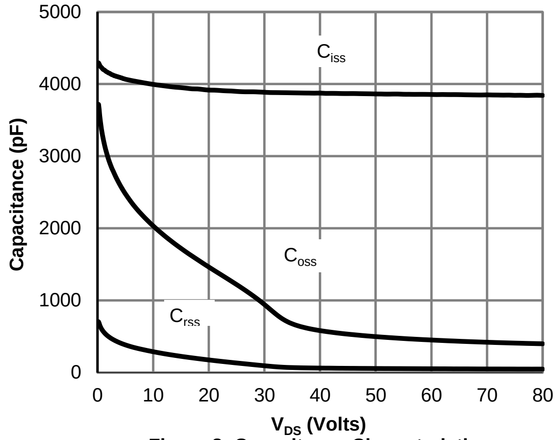


Figure 8: Capacitance Characteristics

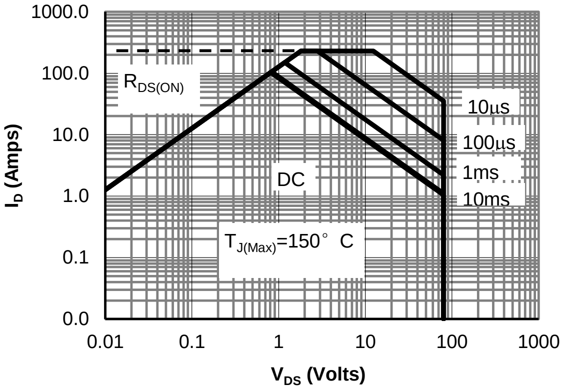


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

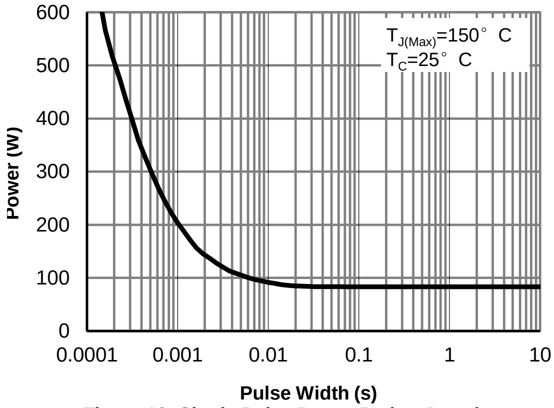


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

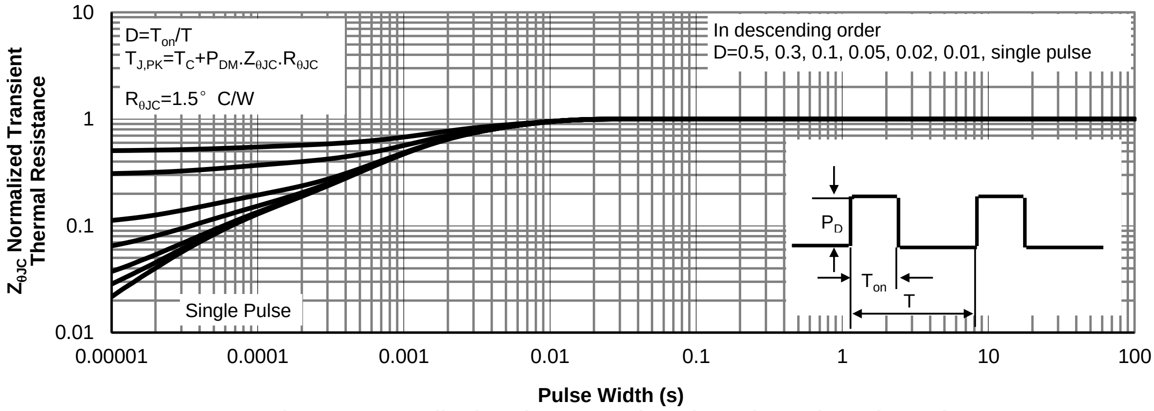


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

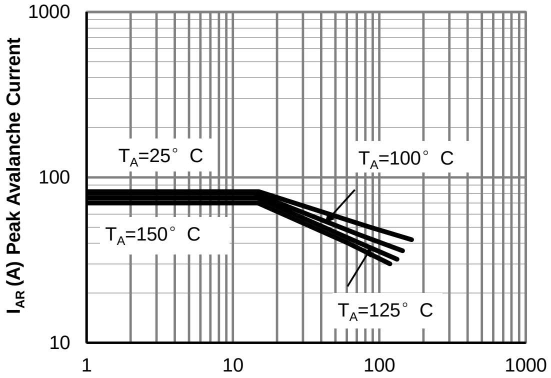


Figure 12: Single Pulse Avalanche capability (Note C)

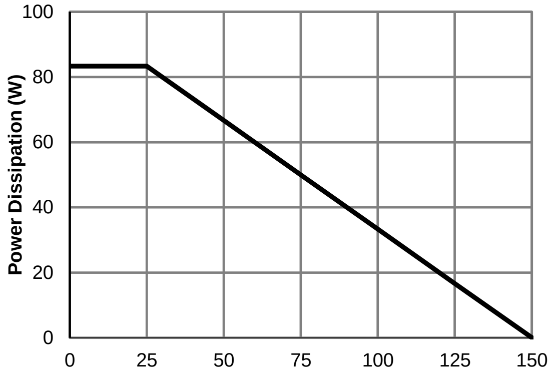


Figure 13: Power De-rating (Note F)

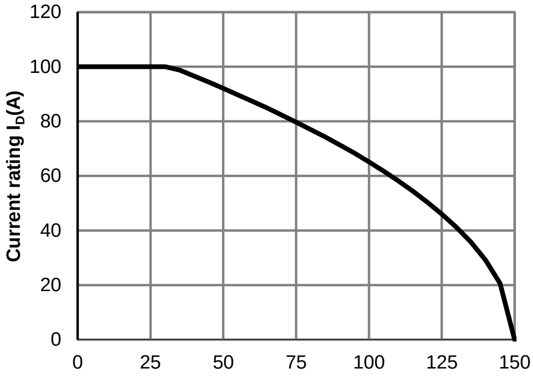


Figure 14: Current De-rating (Note F)

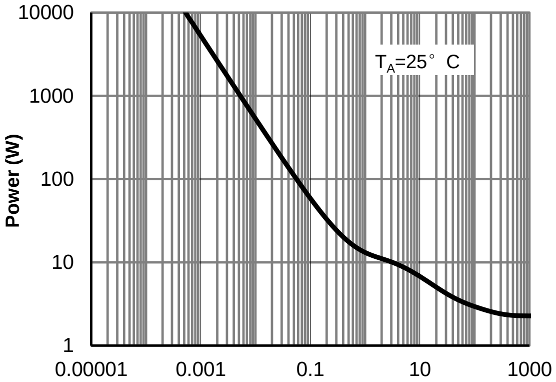


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note G)

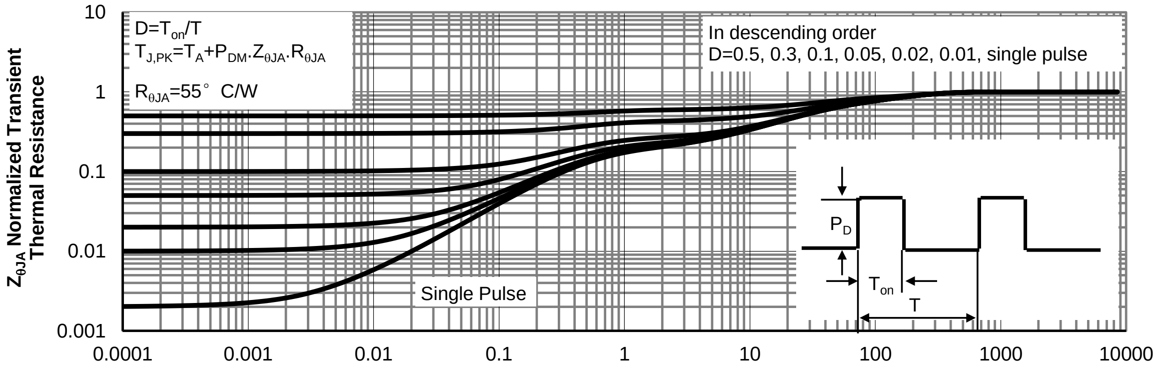
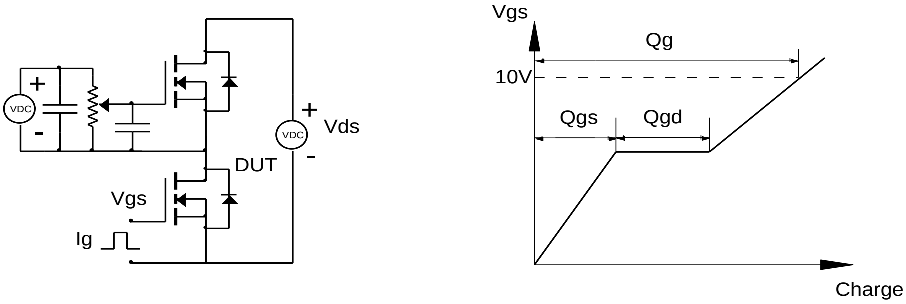
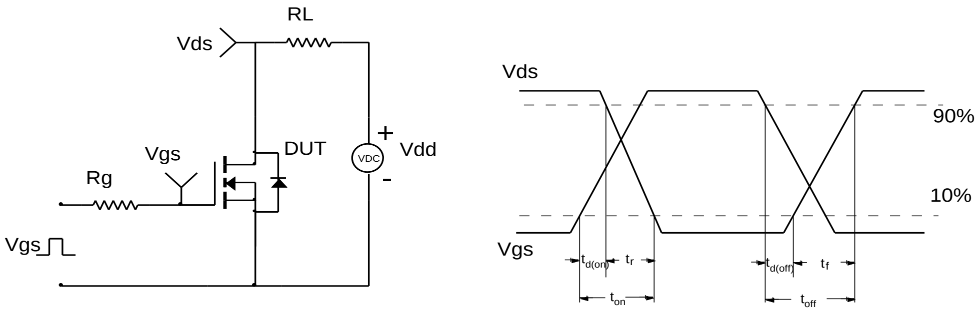


Figure 16: Normalized Maximum Transient Thermal Impedance (Note G)

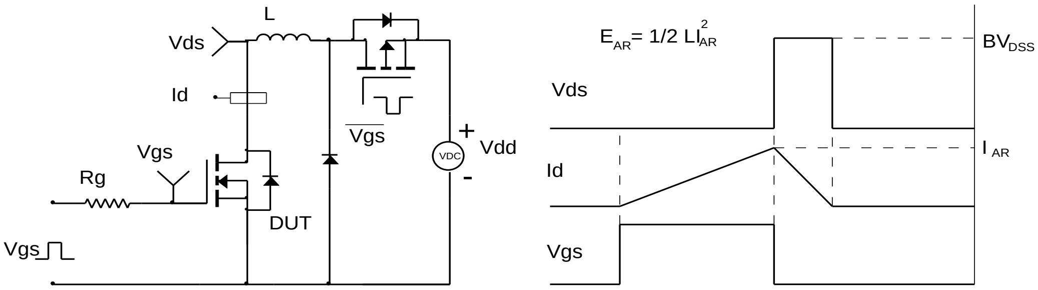
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms